

2N3789 2N3791  
2N3790 2N3792

**SILICON  
PNP POWER TRANSISTORS**



**TO-3 CASE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N3789, 2N3790, 2N3791, and 2N3792 are silicon PNP power transistors, manufactured by the epitaxial planar process, designed for medium speed switching and amplifier applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_C=25^\circ\text{C}$ )

Collector-Base Voltage  
Collector-Emitter Voltage  
Emitter-Base Voltage  
Continuous Collector Current  
Continuous Base Current  
Power Dissipation  
Operating and Storage Junction Temperature  
Thermal Resistance

SYMBOL	2N3789		2N3790		UNITS
	2N3791		2N3792		
$V_{CBO}$	60		80		V
$V_{CEO}$	60		80		V
$V_{EBO}$		7.0			V
$I_C$		10			A
$I_B$		4.0			A
$P_D$		150			W
$T_J, T_{stg}$		-65 to +200			$^\circ\text{C}$
$\theta_{JC}$		1.17			$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3789		2N3790		UNITS
		2N3791		2N3792		
		MIN	MAX	MIN	MAX	
$I_{CEV}$	$V_{CE}=\text{Rated } V_{CEO}, V_{EB}=1.5\text{V}$	-	1.0	-	1.0	mA
$I_{CEV}$	$V_{CE}=\text{Rated } V_{CEO}, V_{EB}=1.5\text{V}, T_C=150^\circ\text{C}$	-	5.0	-	5.0	mA
$I_{EBO}$	$V_{EB}=7.0\text{V}$	-	5.0	-	5.0	mA
$BV_{CEO}$	$I_C=200\text{mA}$	60	-	80	-	V
$V_{CE(SAT)}$	$I_C=4.0\text{A}, I_B=400\text{mA}$ (2N3789, 2N3790)	-	1.0	-	1.0	V
$V_{CE(SAT)}$	$I_C=5.0\text{A}, I_B=500\text{mA}$ (2N3791, 2N3792)	-	1.0	-	1.0	V
$V_{BE(ON)}$	$V_{CE}=2.0\text{V}, I_C=5.0\text{A}$ (2N3789, 2N3790)	-	2.0	-	2.0	V
$V_{BE(ON)}$	$V_{CE}=2.0\text{V}, I_C=5.0\text{A}$ (2N3791, 2N3792)	-	1.8	-	1.8	V
$V_{BE(ON)}$	$V_{CE}=4.0\text{V}, I_C=10\text{A}$	-	4.0	-	4.0	V
$h_{FE}$	$V_{CE}=2.0\text{V}, I_C=1.0\text{A}$ (2N3789, 2N3790)	25	90	25	90	
$h_{FE}$	$V_{CE}=2.0\text{V}, I_C=1.0\text{A}$ (2N3791, 2N3792)	50	180	50	180	
$h_{FE}$	$V_{CE}=2.0\text{V}, I_C=3.0\text{A}$ (2N3789, 2N3790)	15	-	15	-	
$h_{FE}$	$V_{CE}=2.0\text{V}, I_C=3.0\text{A}$ (2N3791, 2N3792)	30	-	30	-	
$f_T$	$V_{CE}=10\text{V}, I_C=500\text{mA}, f=1.0\text{MHz}$	4.0	-	4.0	-	MHz

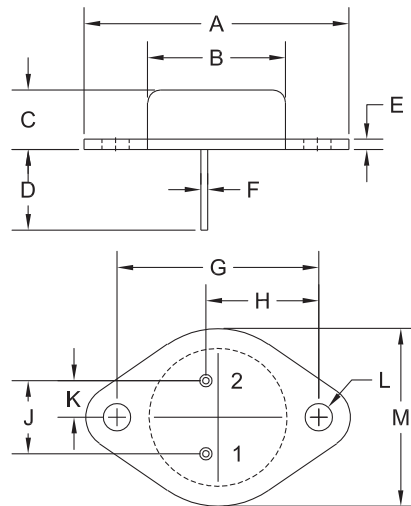
R2 (31-July 2013)

2N3789 2N3791  
2N3790 2N3792

SILICON  
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TO-3 CASE - MECHANICAL OUTLINE



R2

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.516	1.573	38.50	39.96
B (DIA)	0.748	0.875	19.00	22.23
C	0.250	0.450	6.35	11.43
D	0.433	0.516	11.00	13.10
E	0.054	0.065	1.38	1.65
F	0.035	0.045	0.90	1.15
G	1.177	1.197	29.90	30.40
H	0.650	0.681	16.50	17.30
J	0.420	0.440	10.67	11.18
K	0.205	0.225	5.21	5.72
L (DIA)	0.151	0.172	3.84	4.36
M	0.984	1.050	25.00	26.67

TO-3 (REV: R2)

LEAD CODE:

- 1) Base
- 2) Emitter
- Case) Collector

MARKING:

FULL PART NUMBER

R2 (31-July 2013)